



# Mitigate Degradation through Advanced Manufacturing

*Richard Qian 5 Nov 2020*

**LONGI**

# PERC mono c-Si and Degradation

- **Natural degradation due to aging**
- **Potential Induced Degradation (PID)**
- **Light Induced Degradation (LID):**

Well known effect, impacting in the first several hours of the testing

Known mechanisms: Mainly due to Boron Oxygen complex formation (BO LID)

- **Light and elevated Temperature Induced Degradation (LeTID):**

Occurs at elevated temperatures  $> 50^{\circ}\text{C}$  under illumination

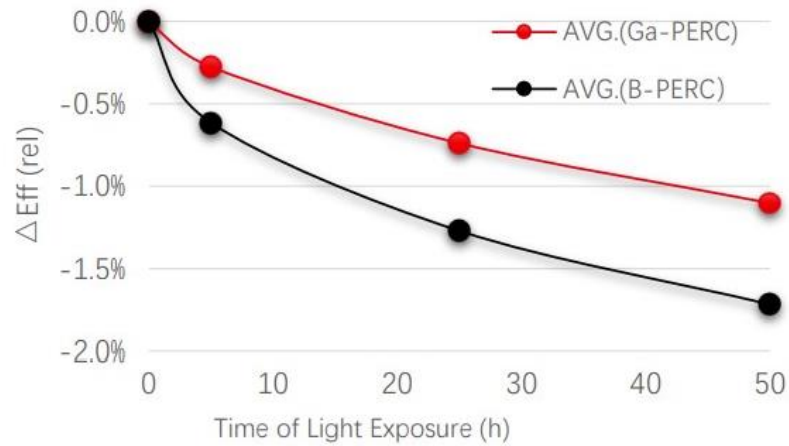
Slower degradation rate, followed by a much slower recovery

Unknown mechanisms: Possibly due to hydrogen diffusion in the bulk or hydrogen related defect activation

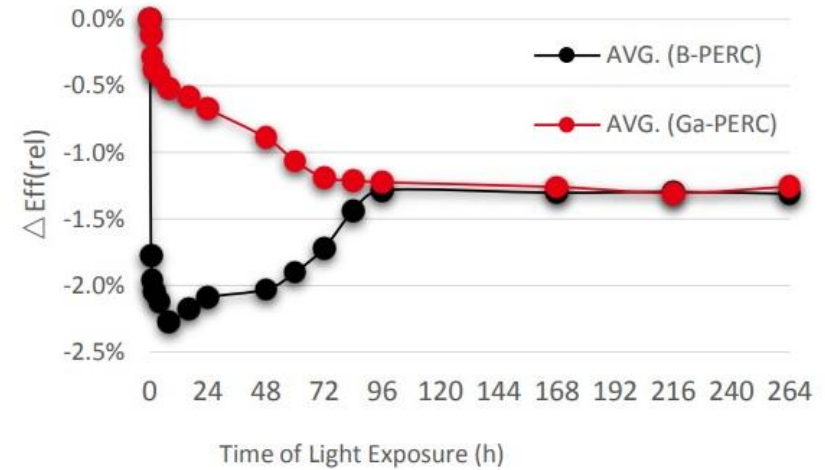
# Solutions

Hydrogenation (2017)

Gallium doping (2020)



Source: LONGi Whitepaper



Ga doped P type mono wafer effectively eliminate LID and LeTID

# Solutions

## BOM selection

- Select and verify material combination (BOM) through sophisticated process
- Internal and 3<sup>rd</sup>-party testing (standard, and accelerated long sequential)
- 3<sup>rd</sup> party LID and LeTID test



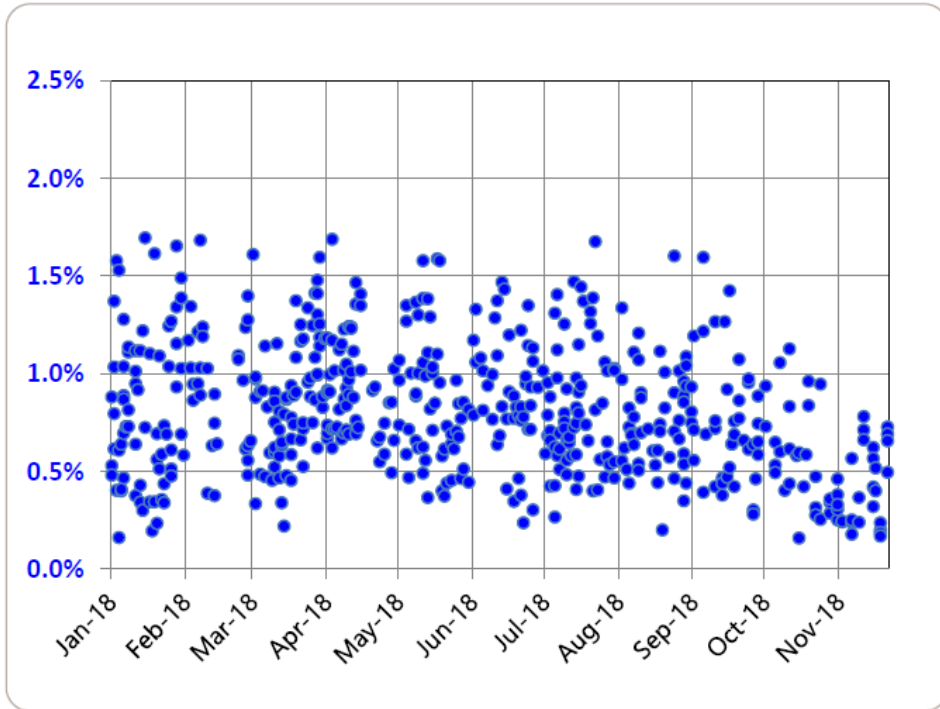


# Solutions

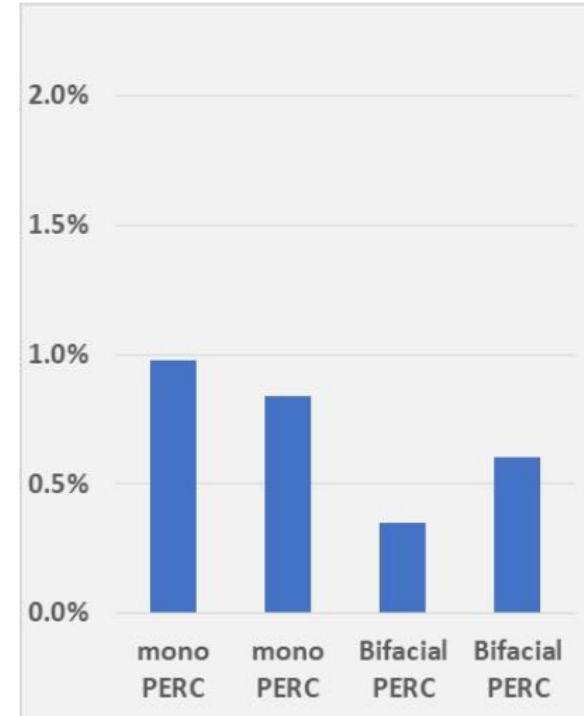
Optimize manufacturing process

Sample, test and monitor regularly

Daily mono PERC cell LID/LeTID monitoring (at 80C)



Module LeTID Measurement



LONGi internal LeTID test at 75C



**LONGi**

Propelling the transformation

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